High hFE Low VCE (sat) 2SC4495

Silicon NPN Triple Diffused Planar Transistor

Application : Audio Temperature Compensation and General Purpose

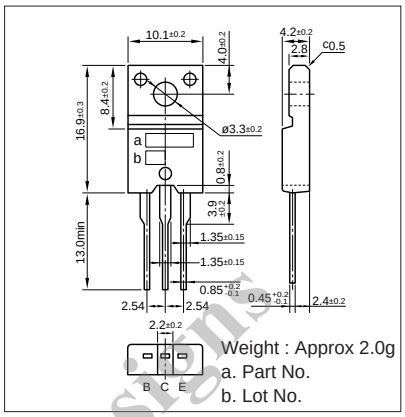
■Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V_{CBO}	80	V
V_{CEO}	50	V
V_{EBO}	6	V
I_C	3	A
I_B	1	A
P_C	25(Tc=25°C)	W
Tj	150	°C
Tstg	–55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I_{CBO}	V_{CB}=80V	10max	μA
I_{EBO}	V_{EB}=6V	10max	μA
$V_{(BR)CEO}$	I_C=25mA	50min	V
h_{FE}	V_{CE}=4V, I_C=0.5A	500min	
$V_{CE(sat)}$	I_C=1A, I_B=20mA	0.5max	V
f_T	V_{CE}=12V, I_E=–0.1A	40typ	MHz
C_{OB}	V_{CB}=10V,f=1MHz	30typ	pF

External Dimensions FM20(TO220F)

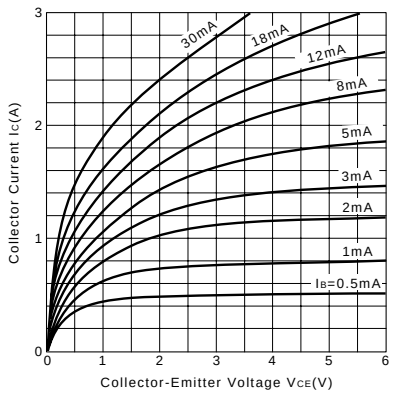


Weight : Approx 2.0g
a. Part No.
b. Lot No.

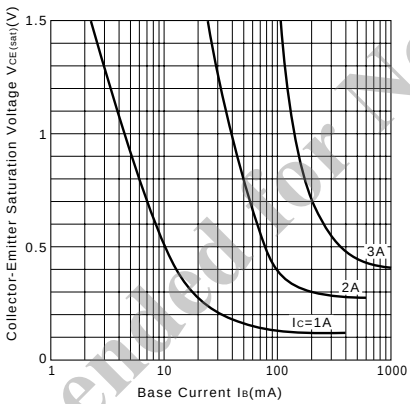
■Typical Switching Characteristics (Common Emitter)

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{BB1} (V)	V_{BB2} (V)	I_{B1} (mA)	I_{B2} (mA)	ton (μs)	tstg (μs)	tf (μs)
20	20	1	10	–5	15	–30	0.45typ	1.60typ	0.85typ

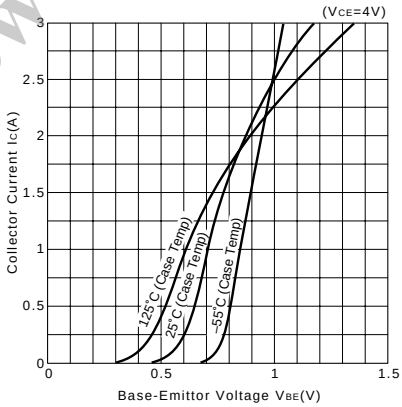
I_C–V_{CE} Characteristics (Typical)



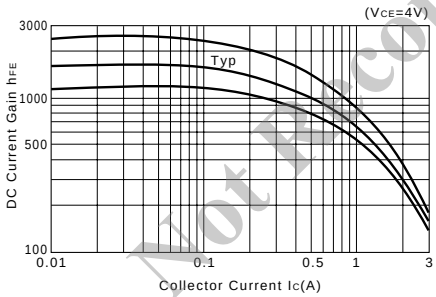
V_{CE}(sat)–I_B Characteristics (Typical)



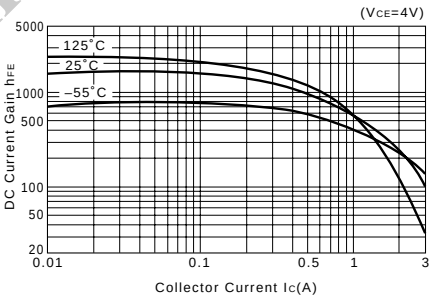
I_C–V_{BE} Temperature Characteristics (Typical)



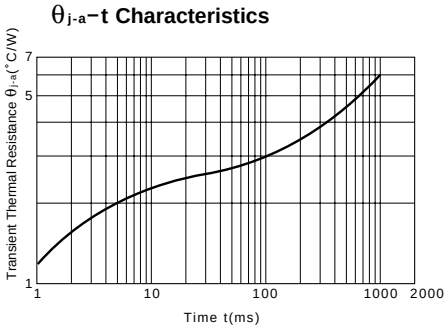
h_{FE}–I_C Characteristics (Typical)



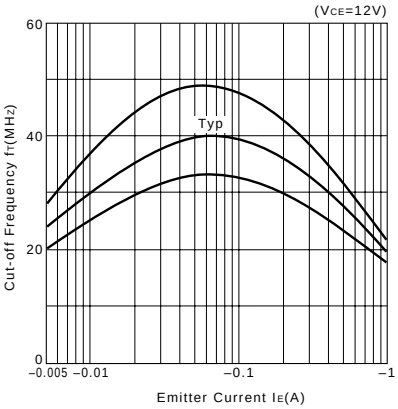
h_{FE}–I_C Temperature Characteristics (Typical)



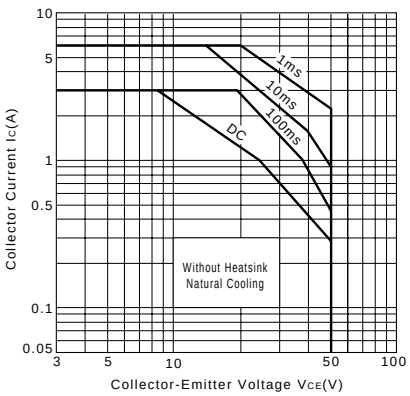
$\theta_{j\text{-}a}$–t Characteristics



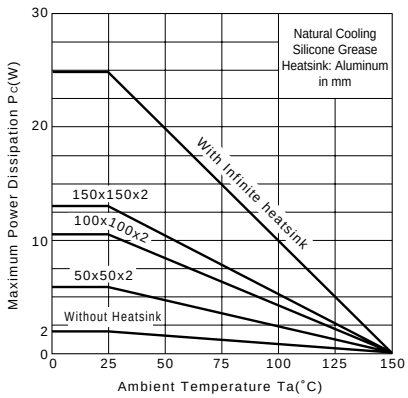
f_T–I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc–Ta Derating



Not Recommended for New Designs